

Performance

- Technology: 0.5um Power GaN HEMT
- Frequency: 0.41~0.61GHz
- Typical Pout: 56dBm
- Typical Gain: 17dB
- Typical PAE: 70%
- Bias: 42V/-3V
- Package: Metal Ceramic

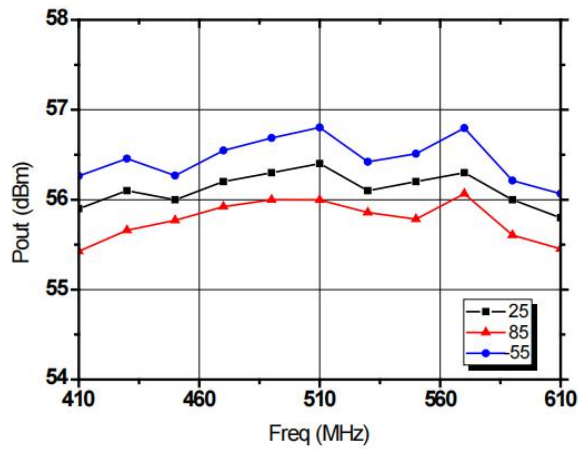


Electrical Specifications ($T_A=25^{\circ}\text{C}$, $V_d=42\text{V}$ (PL=1.3ms, D.C=35%), $V_g=-3\text{V}$, F: 0.41~0.61GHz)

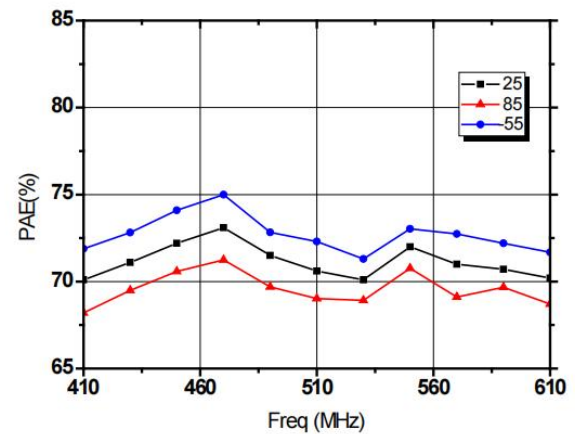
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	56	-	dBm
Gp	Power Gain	-	17	-	dB
η_{add}	Power Added Efficiency	-	70	-	%

Test Curves

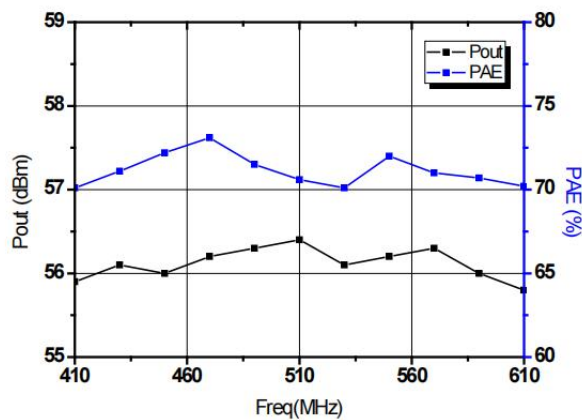
Pout&Freq. @ Different Temp.



PAE&Freq. @ Different Temp.



Pout, PAE&Freq.

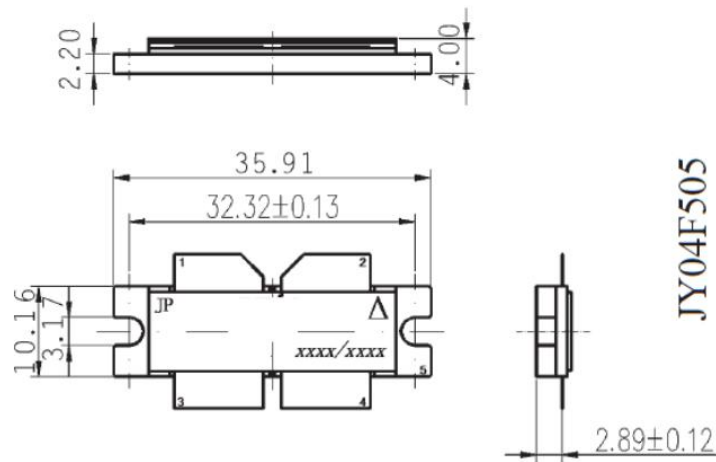


Absolute Max Ratings (T_A=25°C)

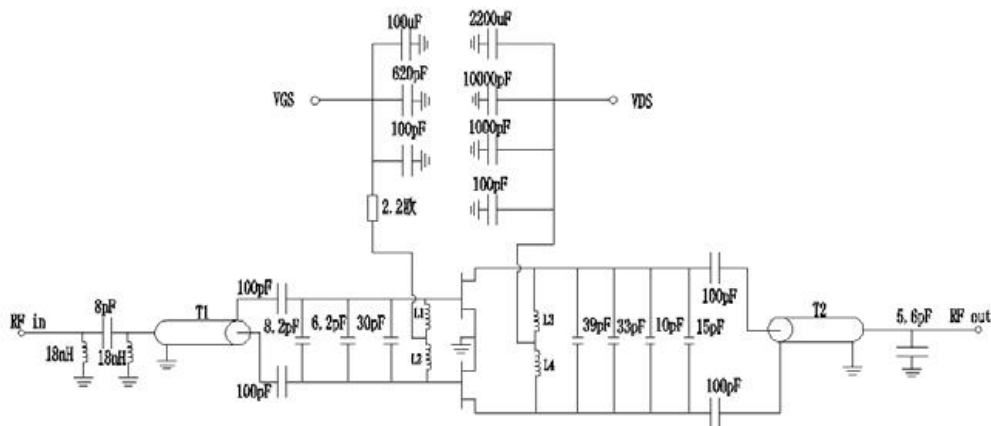
Symbol	Parameter	Value	Remark
V _d	Drain Voltage	50V	
V _g	Grid Voltage	-5V	
T _{ch}	Channel Temperature	225°C	【1】
T _m	Mounting Temperature	300°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~150°C	
T _c	Operating Temperature	-55~85°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing



Application Circuit



Note:

- (1) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;
- (2) In order to ensure the good performance of the power module, the capacity value of the power filter and the energy storage capacitor shall be reasonably selected according to the modulation mode during pulse operation;
- (3) The power-on sequence must be grid first and then drain. The power tube notch leg is the drain end.